

VRRM	IF (TC≤135°C)	QC
1200V	55A	213nC

Applications:

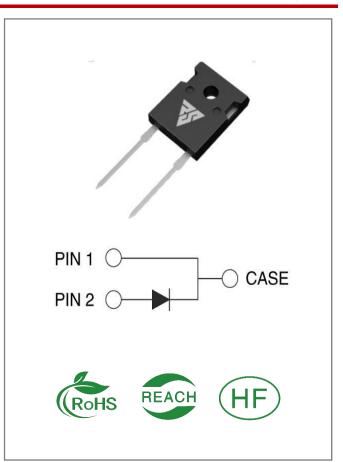
- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Features:

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on VF
- Temperature-independent Switching
- 175°C Operating Junction Temperature

Benefits:

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses



Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSS40120W	TO-247-2	RSS40120W	Tube	30 PCS



Maximum Ratings (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
VRRM	Repetitive Peak Reverse Voltage	1200	V	TC = 25℃	
VRSM	Surge Peak Reverse Voltage	1200	V	TC = 25℃	
VR	DC Blocking Voltage	1200	V	TC = 25°C	
IF	Forward Current	113 55 40	А	TC ≤ 25°C TC ≤ 135°C TC ≤ 152°C	Fig.3
IFSM	Non-Repetitive Forward Surge Current	249 207	А	TC = 25° C, tp = 10ms, Half Sine Wave TC = 110° C, tp = 10ms, Half Sine Wave	
IFRM	Repetitive Peak Forward Surge Current		Α	TC = 25° C, tp = 10ms, Half Sine Wave	
Ptot	Power Dissipation	595	W	TC = 25°C	Fig.4
TC	Maximum Case Temperature	152	$^{\circ}$		
TJ,TST G	Operating Junction and Storage Temperature	-55 to175	$^{\circ}$		

Electrical Characteristics (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
VF	Forward Voltage	1.5 2.22	1.7 -	V	IF = 40A, TJ = 25°C IF = 40A, TJ = 175°C	Fig.1
IR	Reverse Current	9 37	150 -	μΑ	VR = 1200V, TJ = 25°C VR = 1200V, TJ = 175°C	Fig.2
С	Total Capacitance	231 819 4 156	/	pF	VR = 1V, TJ = 25°C, f = 1MHz VR = 400V, TJ = 25°C, f = 1MHz VR = 800V, TJ = 25°C, f = 1MHz	Fig.5
QC	Total Capacitive Charge	213	/	nC	VR =800V,	Fig.6
Ec	Capacitance Stored Energy	64		uJ	VR =800V,	Fig.7

Thermal Characteristics (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Тур.	Unit	Note
RθJC	Thermal Resistance from Junction to Case	0.252	°C/W	Fig.8



Typical Feature Curve

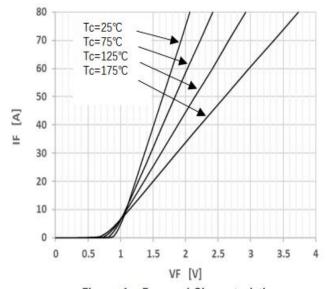


Figure 1 Forward Characteristics

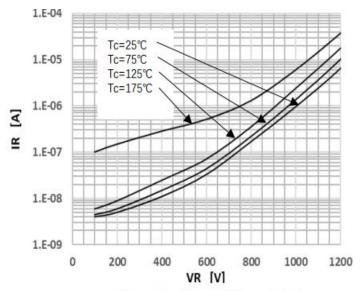


Figure 2 Reverse Characteristics

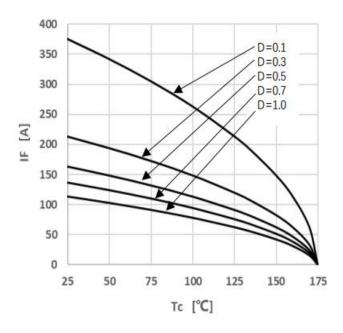


Figure 3 Peak Forward Current Derating

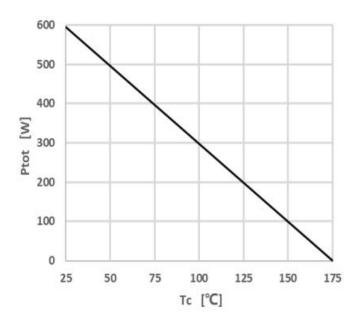


Figure 4 Power Dissipation



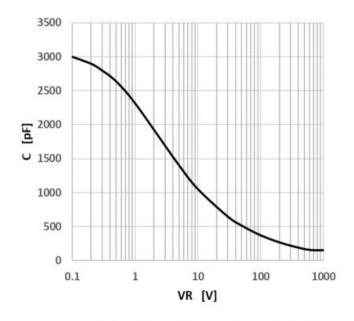


Figure 5 Capacitance vs. Reverse Voltage

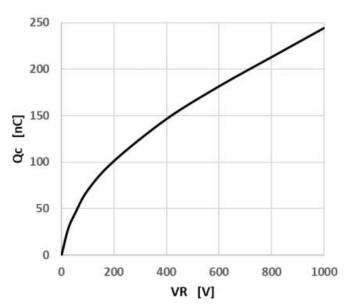


Figure 6 Capacitance Charge vs. Reverse Voltage

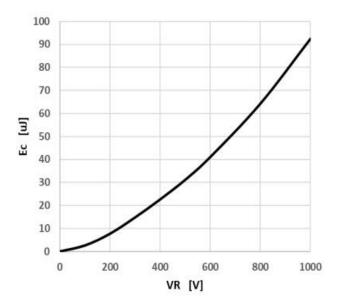


Figure 7 Capacitance Stored Energy

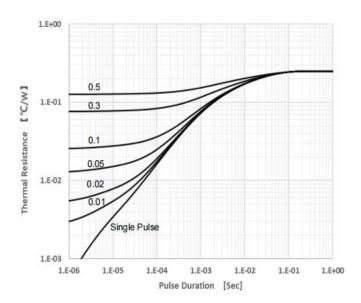
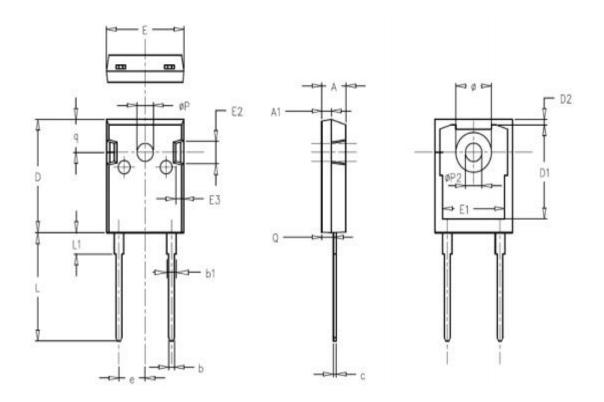


Figure 8 Transient Thermal Impedance



Package outline drawing(TO-247-2 Unit: mm)



SYMBOL	MILLIMETERS		N OTTS SWIPOL	MILLIMETERS			и отто		
	N ormal	MIN.	MAX.	N OTES	SYMBOL	Normal	MIN.	MAX.	N OTES
Α	4.98	4.68	5.36		øΡ	3.66	3.45	3.85	
A 1	1.99	1.90	2.10		е	5.44	BSC	:	
Q	2.41	2.30	2.60	Ĭ,	q	6.24	5.99	6.58	
С	0.60	0.48	0.72		øP2	3.45	3.24	3.64	
Ь	1.20	1.00	1.40		ø	7.14	7.10	7.30	
Ь1	2.07	1.90	2.30		D1	16.56	16.10	17.10	
D	21.10	20.80	21.80		D2	0.98	0.80	1.36	
Ε	15.98	15.38	16.20		E1	13.30	13.00	13.52	
L	20.28	19.50	20.50		E2	5.64	5.10	6.10	
L1	4.01	3.75	4.35		E3	2.33	1.90	2.70	

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